

## **Description**

The Si2316DS-T1-E3 uses advanced trench technology to provide excellent  $R_{\rm DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



#### **SOT-23**

#### **General Features**

 $V_{DS} = 30V I_D = 4A$ 

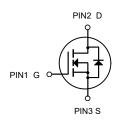
 $R_{DS(ON)}$  < 38m $\Omega$  @  $V_{GS}$ =10V

# Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

## **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
Si2316DS-T1-E3	SOT-23	HXY MOSFET	3000

## Absolute Maximum Ratings (T<sub>A</sub>=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>G</sub> s	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current-Continuous	4	А
Ідм	Drain Current-Pulsed (Note 1)	16.4	А
P <sub>D</sub>	Maximum Power Dissipation	1	W
TJ,Tstg	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	125	°C/W



# Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units	
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	30	-	-	V	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V,	-	-	1.0	μA	
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V	-	-	±100	nA	
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1.0	1.5	2.5	V	
D	Static Drain-Source on-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =4A	-	29	38	mΩ	
$R_{DS(on)}$		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A	-	45	65	11122	
$C_{iss}$	Input Capacitance	\\ 45\\\\\ 0\\	-	233	_	pF	
Coss	Output Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1.0MHz	-	44	-	pF	
Crss	Reverse Transfer Capacitance	T=1.UMHZ	-	33	-	pF	
Qg	Total Gate Charge	V <sub>DS</sub> =15V, I <sub>D</sub> =2A, V <sub>GS</sub> =10V	-	3	-	nC	
Qgs	Gate-Source Charge		-	0.5	-	nC	
$Q_{gd}$	Gate-Drain("Miller") Charge		-	0.8	-	nC	
t <sub>d(on)</sub>	Turn-on Delay Time	\/ -45\/	-	4	-	ns	
t <sub>r</sub>	Turn-on Rise Time	V <sub>DS</sub> =15V,	-	2.1	-	ns	
t <sub>d(off)</sub>	Turn-off Delay Time	$I_D=4A$ , $R_{GEN}=3\Omega$ ,	-	15	-	ns	
t <sub>f</sub>	Turn-off Fall Time	V <sub>GS</sub> =10V	-	3.2	-	ns	
	Maximum Continuous Drain to Source Diode Forward Current				4	^	
ls			-	-	4	Α	
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	16	Α	
V <sub>SD</sub>	Drain to Source Diode Forward			-	1.2	V	
	Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =4A					

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

<sup>2.</sup> Pulse Test: Pulse Width≤300µs, Duty Cycle≤0.5%



## **Typical Characteristics**

Figure1: Output Characteristics

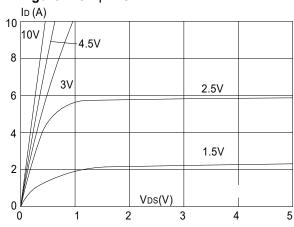


Figure 2: Typical Transfer Characteristics

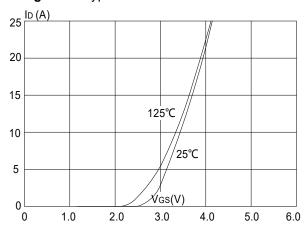


Figure 3:On-resistance vs. Drain Current

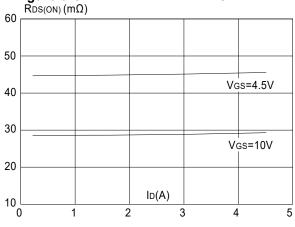


Figure 4: Body Diode Characteristics

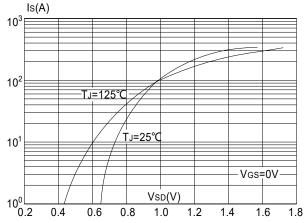


Figure 5: Gate Charge Characteristics

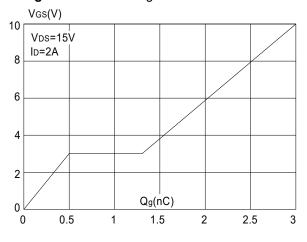
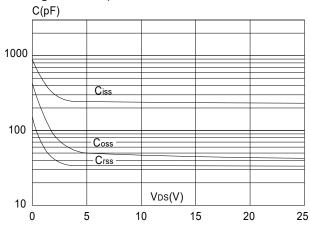
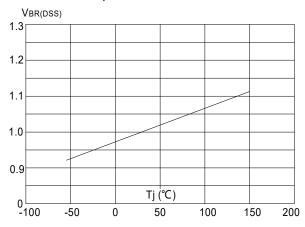


Figure 6: Capacitance Characteristics





**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



**Figure 8:** Normalized on Resistance vs. Junction Temperature

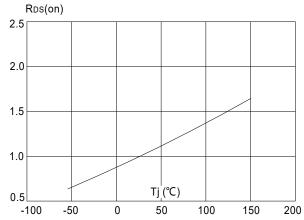
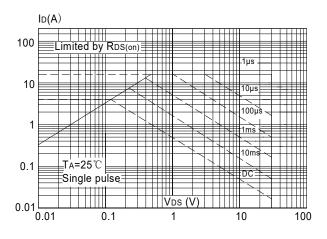
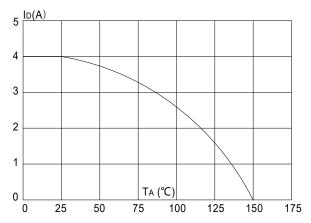


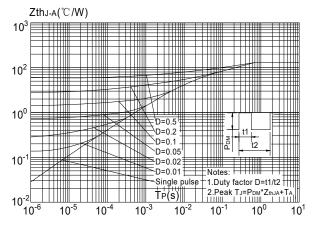
Figure 9: Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature

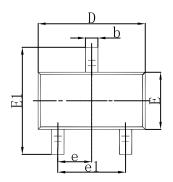


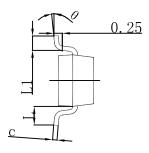
**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

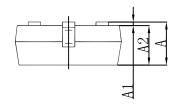




# **SOT-23 Package Outline Dimensions**

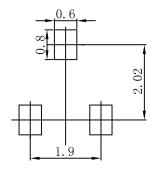






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# **SOT-23 Suggested Pad Layout**



## Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.

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